BYR29X-600

Ultrafast power diode Rev. 02 — 15 July 2010

Product data sheet

Product profile 1.

1.1 General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- Fast switching
- Isolated plastic package
- Low forward voltage drop
- Soft recovery characteristic

1.3 Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- High frequency switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\bar{\delta} = 0.5$; [1] $T_h \le 73$ °C; see Figure 1; see Figure 2; see Figure 3	-	-	8	Α
I _{FSM}	non-repetitive peak forward current	$T_{j(init)}$ = 25 °C; t_p = 10 ms; sine-wave pulse	-	-	60	Α
Static char	racteristics					
V _F	forward voltage	$I_F = 8 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 5</u>	-	1.07	1.5	V
Dynamic c	haracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 8; see Figure 7	-	60	75	ns

^[1] Neglecting switching and reverse current losses



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		w 14 .
2	Α	anode	mb	K — A 001aaa020
mb	n.c.	mounting base; isolated		
			SOD113 (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	r Package			
	Name	Description	Version	
BYR29X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	T _h ≤ 136 °C; DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; $T_h \le 73$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	[1] -	8	Α
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t_p = 25 $\mu s;$ $T_h \leq 73$ °C	-	16	Α
I _{FSM}	non-repetitive peak forward	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	60	Α
	current	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	66	Α
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

[1] Neglecting switching and reverse current losses

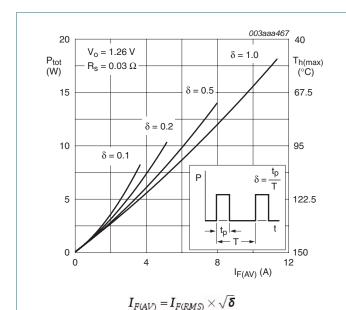
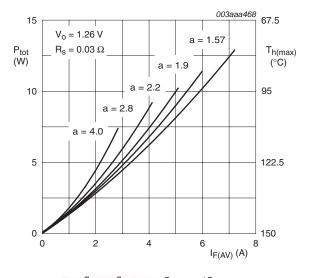
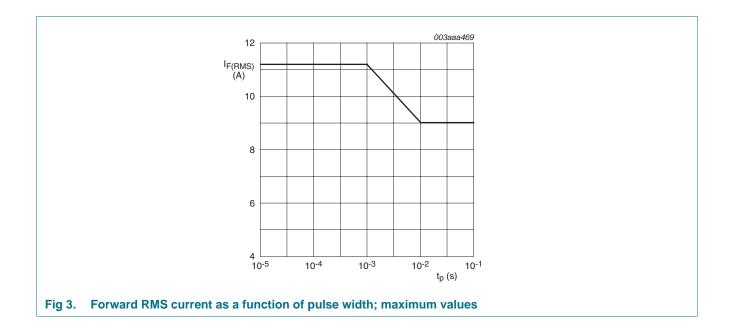


Fig 1. Forward power dissipation and permissible heatsink temperature as a function of average forward current; square waveform; maximum values



a =form factor $= I_{T(RMS)} / I_{T(AV)}$

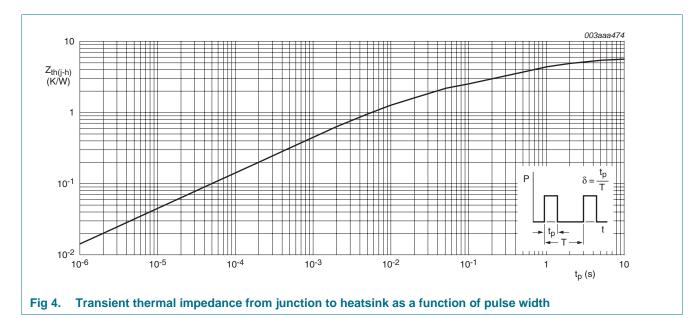
Fig 2. Forward power dissipation and permissible heatsink temperature as a function of average forward current; sinusoidal waveform; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound ; see Figure 4	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

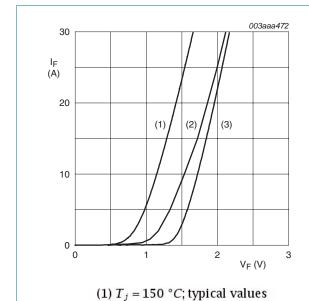
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

Characteristics

Table 7. **Characteristics**

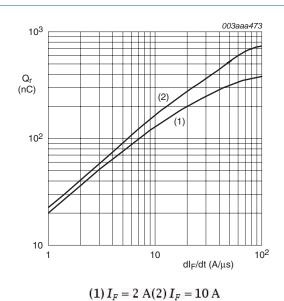
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V_{F}	forward voltage	$I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.75	1.95	V
		$I_F = 8 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.07	1.5	V
		$I_F = 8 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	-	1.7	V
I _R	reverse current	$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.2	mA
		$V_R = 600 \text{ V}; T_j = 25 \text{ °C}$	-	1	10	μΑ
Dynamic ch	naracteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6; see Figure 7	-	150	200	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 8; see Figure 7	-	60	75	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 100 \text{ °C}$; see Figure 9; see Figure 7	-	-	6	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 10	-	5	-	V



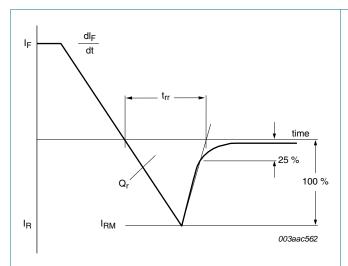
(2) $T_j = 150$ °C; maximum values

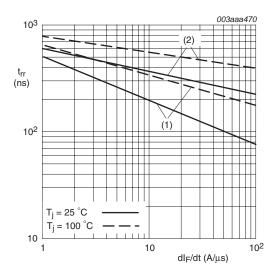
(3) $T_j = 25$ °C; maximum values





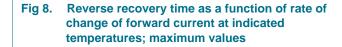
Recovered charge as a function of rate of change of forward current

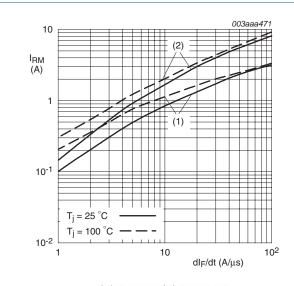




(1) $I_F = 1 \text{ A}(2) I_F = 10 \text{ A}$

Fig 7. Reverse recovery definitions; ramp recovery





(1) $I_F = 1 \text{ A}(2) I_F = 10 \text{ A}$

Fig 9. Peak reverse recovery current as a function of rate of change of forward current at indicated temperatures

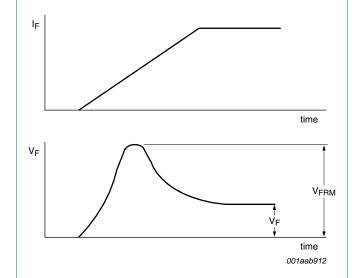


Fig 10. Forward recovery definitions

8. Package outline

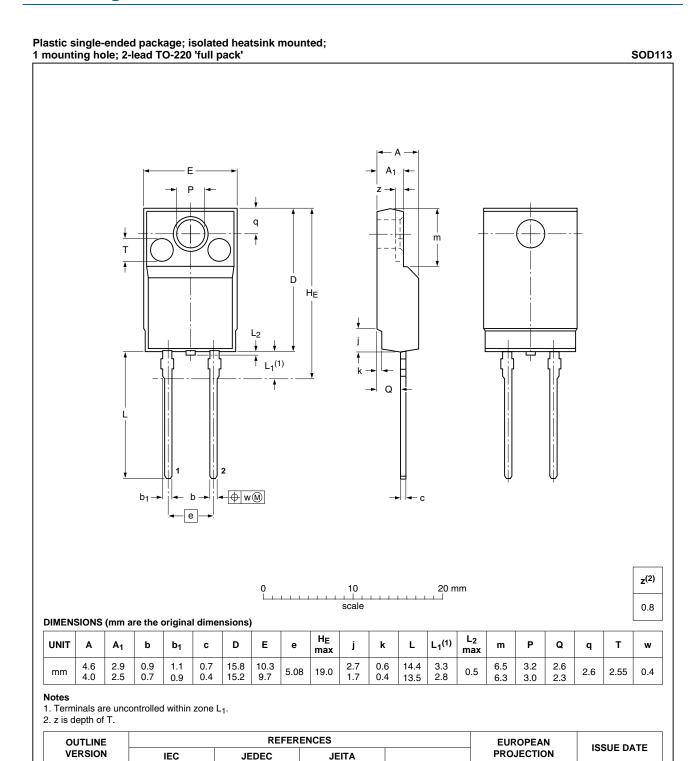


Fig 11. Package outline SOD113 (TO-220F)

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2-lead TO-220F

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SOD113

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Ultrafast power diode

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BYR29X-600 v.2	20100715	Product data sheet	-	BYR29X-600 v.1	
Modifications:	 The format of this of NXP Semiconductor 	this data sheet has been redesigned to comply with the new identity guidelines ductors.			
	 Legal texts have be 	een adapted to the new co	mpany name where ap	opropriate.	
BYR29X-600 v.1 (9397 750 12006)	20030926	Product data	-	-	

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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